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Vishay/Siliconix
SIA850DJ-T1-GE3

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New Product

SiA850DJ

Vishay Siliconix

N-Channel 190-V (D-S) MOSFET with 190-V Diode

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
190	3.8 at V_{GS} = 4.5 V	0.95	1.4 nC
	4.2 at V_{GS} = 2.5 V	0.9	
	17 at V_{GS} = 1.8 V	0.3	

DIODE PRODUCT SUMMARY		
V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A)[a]
190	1.2 at 0.5 A	0.95

FEATURES

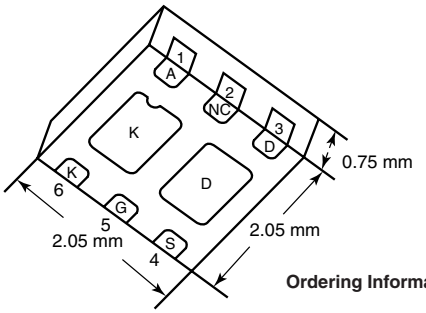
- **Halogen-free According to IEC 61249-2-21**
- LITTLE FOOT® *Plus* Schottky Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
  - Thin 0.75 mm profile

Pb-free
RoHS COMPLIANT
HALOGEN FREE

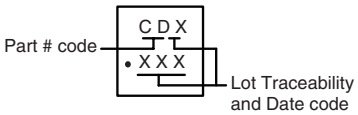
APPLICATIONS

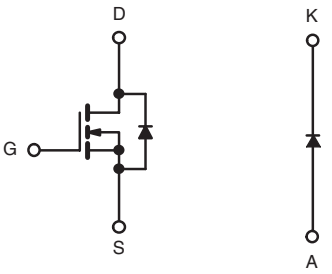
- DC/DC Converter for Portable Devices
- Load Switch for Portable Devices

PowerPAK SC-70-6 Dual



Marking Code





N-Channel MOSFET

Ordering Information: SiA850DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage (MOSFET)		V_{DS}	190	V
Reverse Voltage (Diode)		V_{KA}	190	
Gate-Source Voltage (MOSFET)		V_{GS}	± 16	
Continuous Drain Current (T_J = 150 °C) (MOSFET)	T_C = 25 °C	I_D	0.95	A
	T_C = 70 °C		0.76	
	T_A = 25 °C		0.47[b, c]	
	T_A = 70 °C		0.38[b, c]	
Pulsed Drain Current (MOSFET)		I_{DM}	1	
Continuous Source-Drain Diode Current (MOSFET Diode Conduction)	T_C = 25 °C	I_S	0.95	
	T_A = 25 °C		0.47[b, c]	
Average Forward Current (Diode)		I_F	0.95	
Pulsed Forward Current (Diode)		I_{FM}	2	
Maximum Power Dissipation (MOSFET)	T_C = 25 °C	P_D	7	W
	T_C = 70 °C		5	
	T_A = 25 °C		1.9[b, c]	
	T_A = 70 °C		1.2[b, c]	
Maximum Power Dissipation (Diode)	T_C = 25 °C		7.8	
	T_C = 70 °C		5	
	T_A = 25 °C		1.9[b, c]	
	T_A = 70 °C		1.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)[d, e]			260	

New Product

SiA850DJ

Vishay Siliconix

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET)[b, f]	t ≤ 5 s	R_{thJA}	52	65	°C/W
Maximum Junction-to-Case (Drain) (MOSFET)	Steady State	R_{thJC}	12.5	16	
Maximum Junction-to-Ambient (Diode)[b, f]	t ≤ 5 s	R_{thJA}	52	65	
Maximum Junction-to-Case (Drain) (Diode)	Steady State	R_{thJC}	12.5	16	

Notes:
a. T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 5 s.
d. See Solder Profile (*www.vishay.com/ppg?73257*). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
f. Maximum under Steady State conditions is 110 °C/W.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	190			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		200		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 3.0		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.6		1.4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 16 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 190 V, V_{GS} = 0 V			1	µA
		V_{DS} = 190 V, V_{GS} = 0 V, T_J = 85 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 4.5 V	1			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 0.36 A		3.0	3.8	Ω
		V_{GS} = 2.5 V, I_D = 0.35 A		3.2	4.2	
		V_{GS} = 1.8 V, I_D = 0.15 A		3.5	17.0	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 0.36 A		2		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 100 V, V_{GS} = 0 V, f = 1 MHz		90		pF
Output Capacitance	C_{oss}			5		
Reverse Transfer Capacitance	C_{rss}			3		
Total Gate Charge	Q_g	V_{DS} = 95 V, V_{GS} = 10 V, I_D = 0.47 A		3	4.5	nC
		V_{DS} = 95 V, V_{GS} = 4.5 V, I_D = 0.47 A		1.4	2.1	
Gate-Source Charge	Q_{gs}			0.25		
Gate-Drain Charge	Q_{gd}			0.40		
Gate Resistance	R_g	f = 1 MHz		2.3		Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 95 V, R_L = 250 Ω, I_D ≅ 0.38 A, V_{GEN} = 4.5 V, R_g = 1 Ω		10	15	ns
Rise Time	t_r			15	25	
Turn-Off DelayTime	$t_{d(off)}$			25	40	
Fall Time	t_f			15	25	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 95 V, R_L = 250 Ω, I_D ≅ 0.38 A, V_{GEN} = 10 V, R_g = 1 Ω		3	10	
Rise Time	t_r			12	20	
Turn-Off DelayTime	$t_{d(off)}$			10	15	
Fall Time	t_f			10	15	

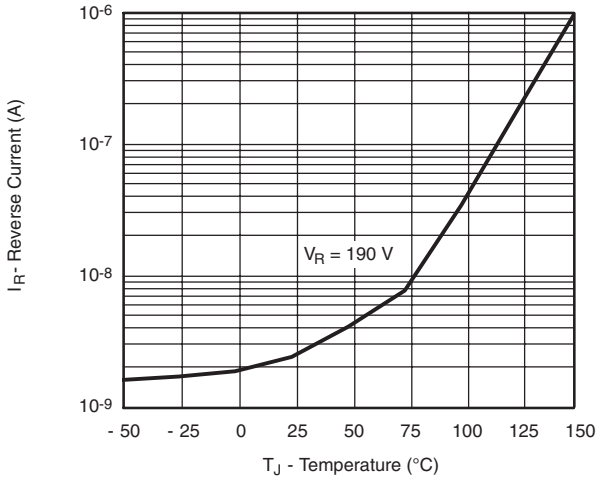
SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			0.95	A
Pulse Diode Forward Current	I_{SM}				1	
Body Diode Voltage	V_{SD}	I_S = 0.5 A, V_{GS} = 0 V		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 0.5 A, dI/dt = 100 A/µs, T_J = 25 °C		45	70	ns
Body Diode Reverse Recovery Charge	Q_{rr}			45	70	nC
Reverse Recovery Fall Time	t_a			21		ns
Reverse Recovery Rise Time	t_b			24		

Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

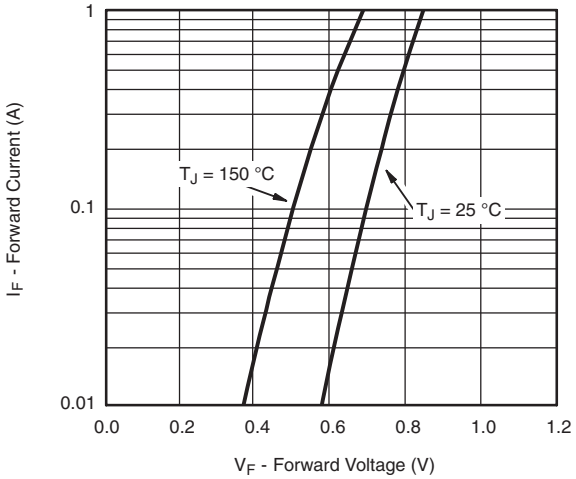
DIODE SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Forward Voltage Drop	V_F	I_F = 0.5 A		0.82	1.2	V
		I_F = 0.5 A, T_J = 125 °C		0.7	1.0	
Maximum Reverse Leakage Current	I_{rm}	V_R = 190 V			1	µA
		V_R = 190 V, T_J = 85 °C			10	
Body Diode Reverse Recovery Time	t_{rr}	I_F = 0.5 A, dI/dt = 100 A/µs, T_J = 25 °C		45	70	ns
Body Diode Reverse Recovery Charge	Q_{rr}			45	70	nC
Reverse Recovery Fall Time	t_a			21		ns
Reverse Recovery Rise Time	t_b			24		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

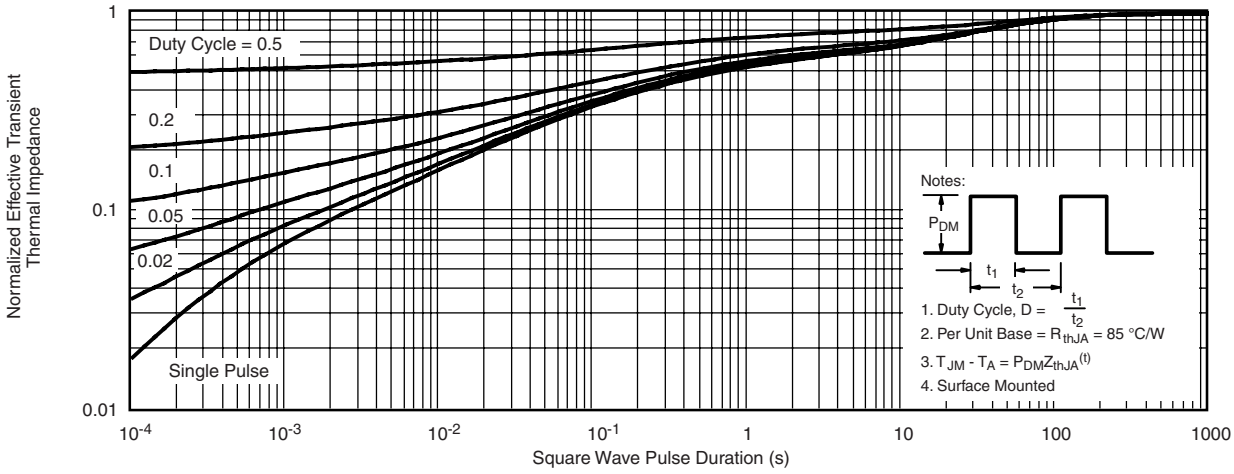
DIODE TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



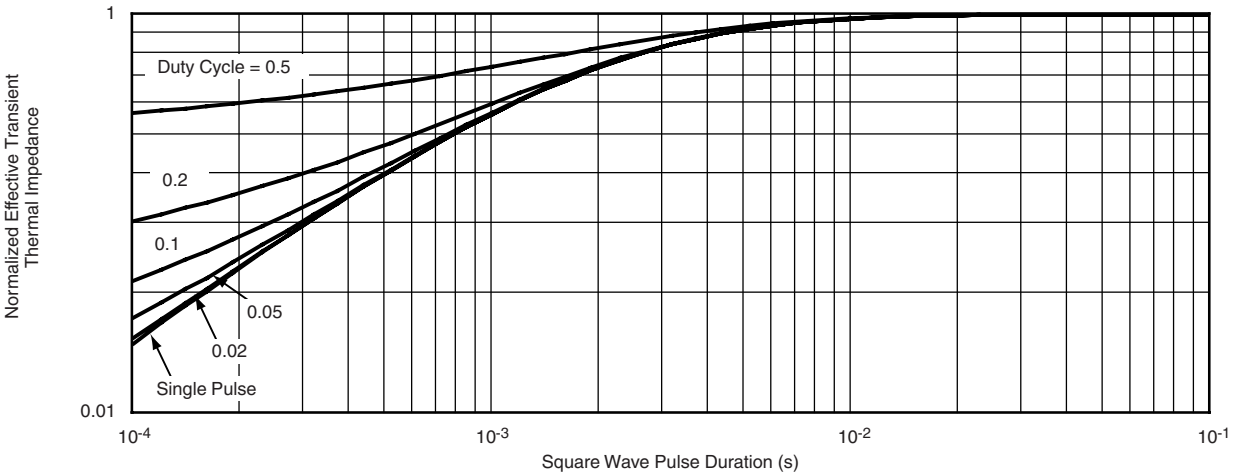
Reverse Current vs. Junction Temperature



Forward Diode Voltage

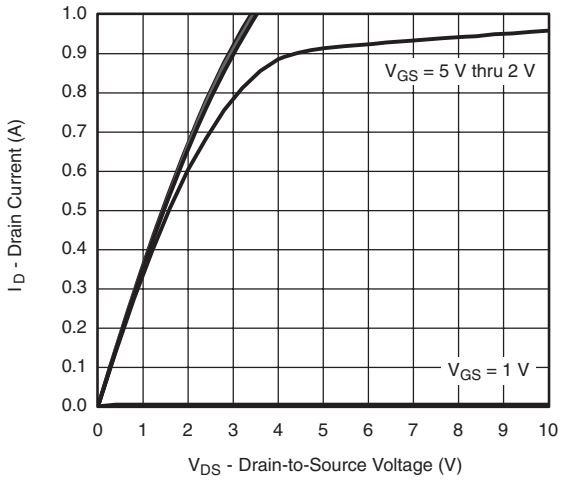


Normalized Thermal Transient Impedance, Junction-to-Ambient

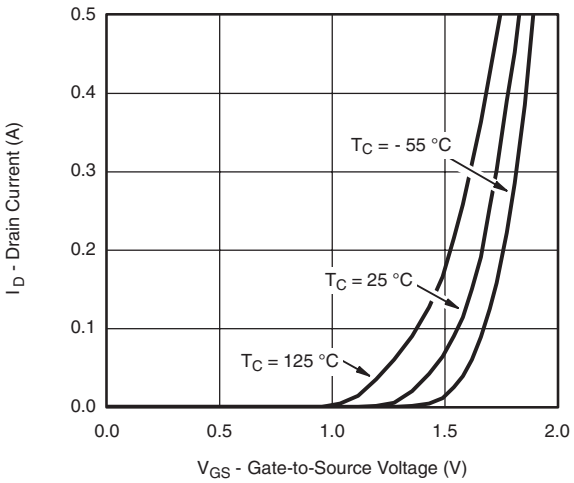


Normalized Thermal Transient Impedance, Junction-to-Case

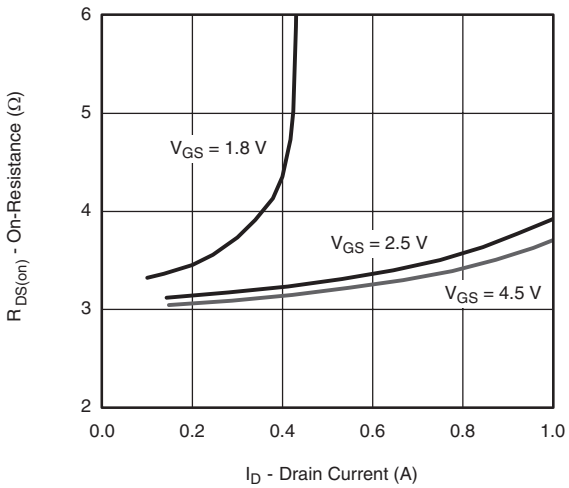
MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



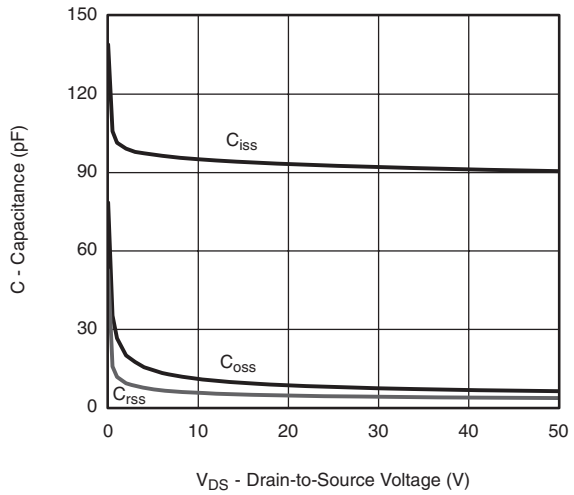
Output Characteristics



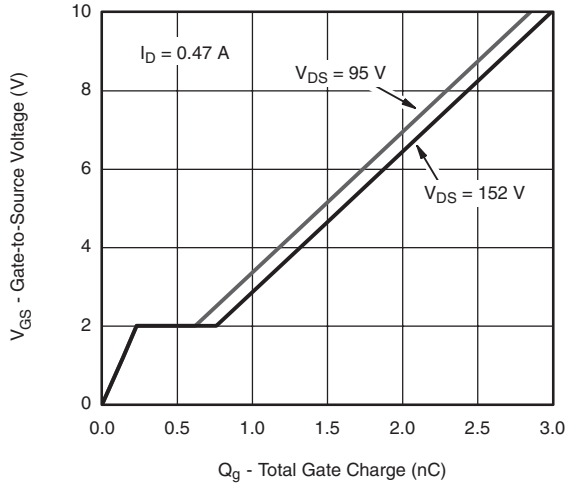
Transfer Characteristics



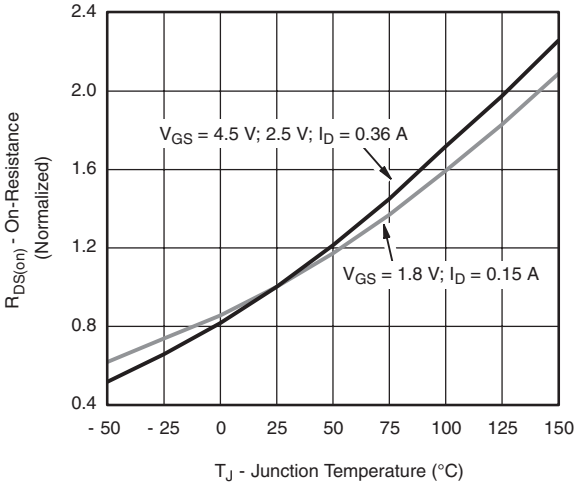
On-Resistance vs. Drain Current



Capacitance

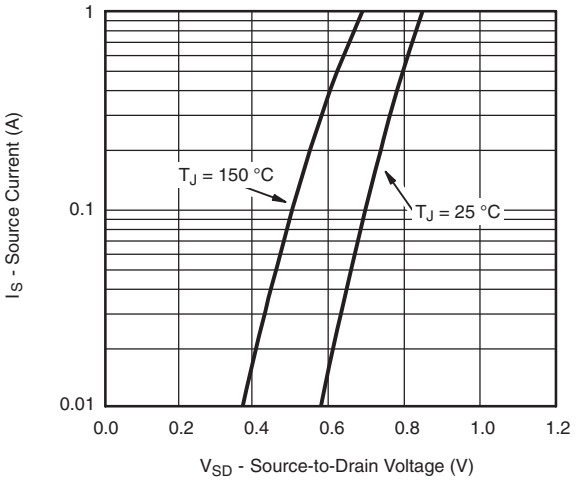


Gate Charge

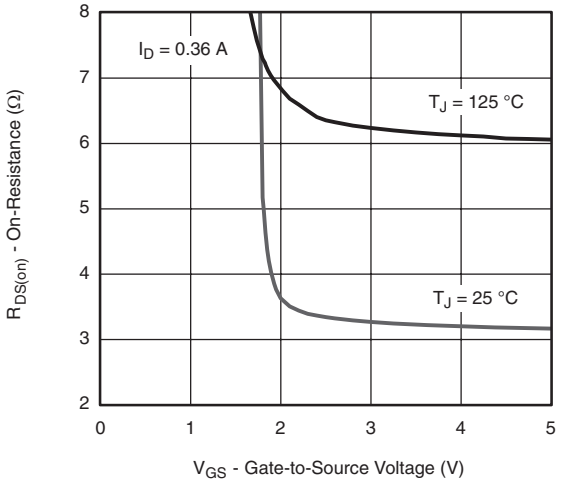


On-Resistance vs. Junction Temperature

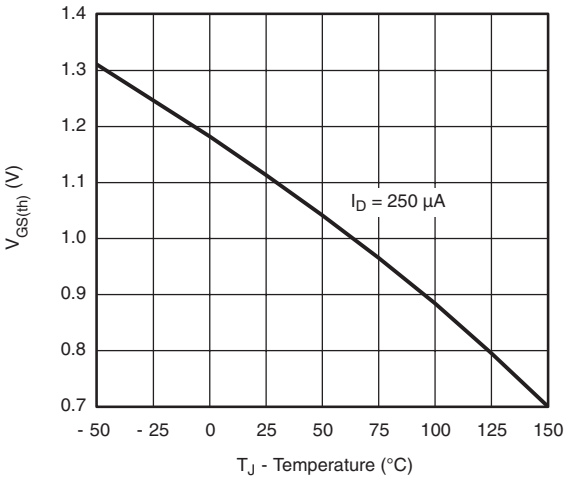
MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



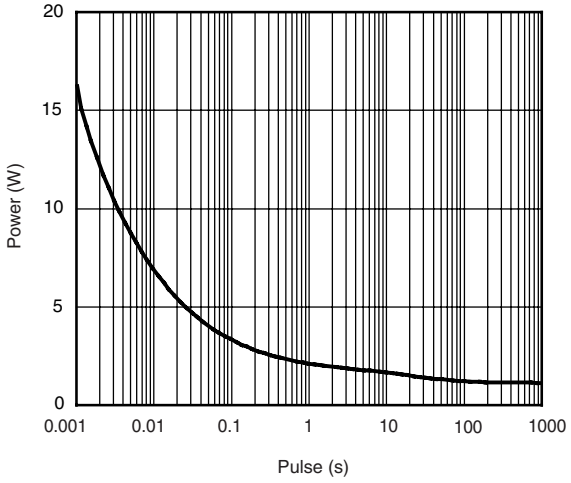
Source-Drain Diode Forward Voltage



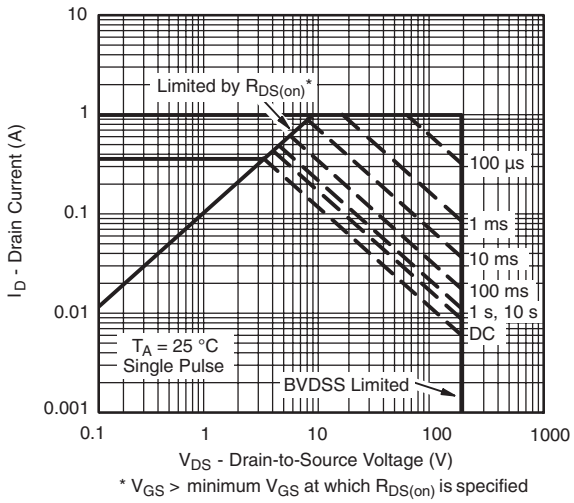
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



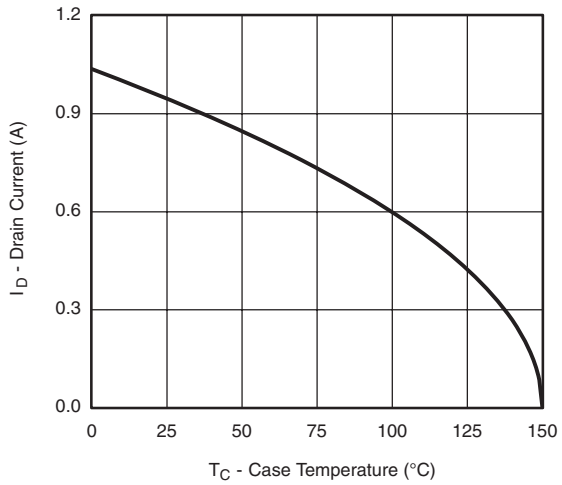
Single Pulse Power (Junction-to-Ambient)



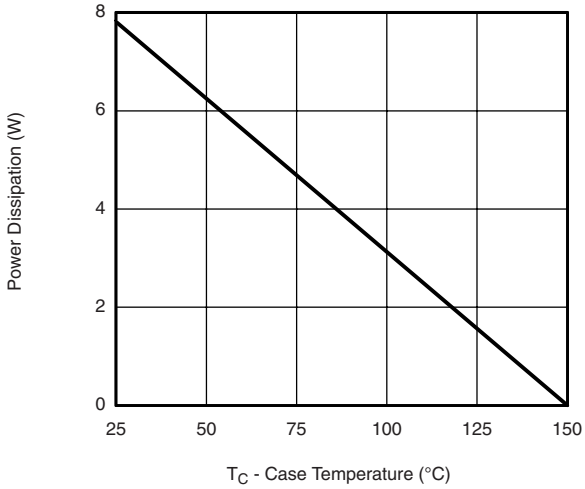
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



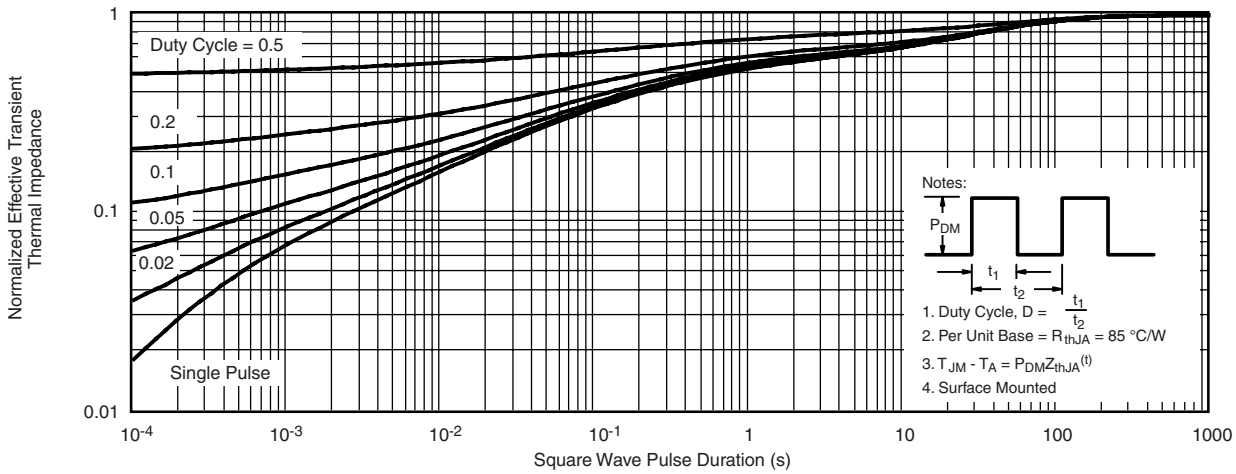
Current Derating*



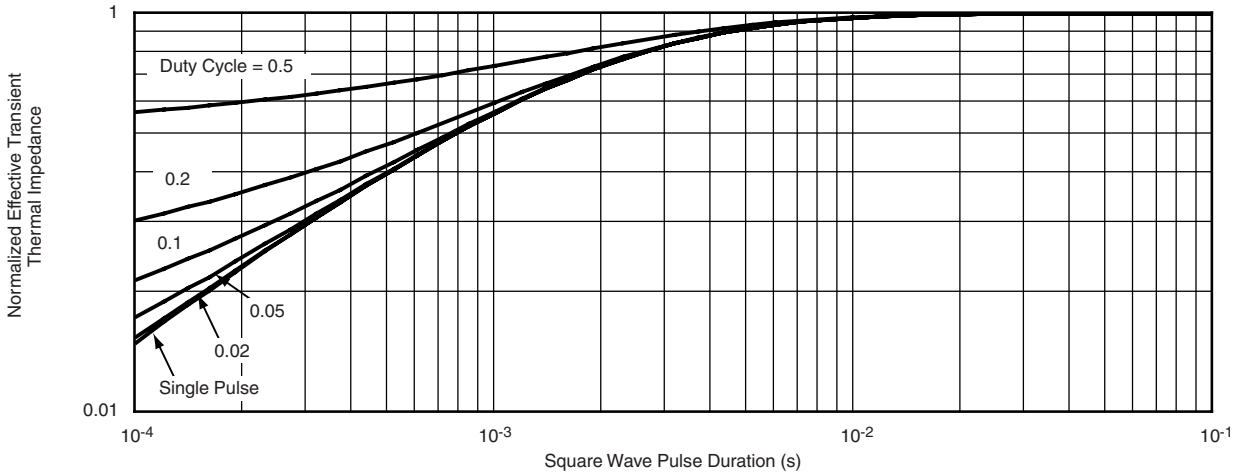
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

MOSFET TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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Vishay

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